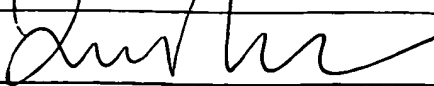


Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>14699-019001</b>	Application No. <b>10/823,004</b>
	Applicant <b>Takao Myono et al.</b>		
	Filing Date <b>April 13, 2004</b>	Group Art Unit <b>2816</b>	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
<u>U</u>	AA	6,515,535	02/04/2003	Myono	327	536	
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Abstract	
							Yes	No
<u>U</u>	AL	2001-286125	10/12/2001	Japan			X	
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
<u>U</u>	AQ	J. F. Dickson, "On-Chip High-Voltage Generation in MNOS Integrated Circuits Using an Improved Voltage Multiplier Technique", IEEE Journal of Solid-State Circuits pp 374-378 (1976)
	AR	
	AS	
	AT	

Examiner Signature 	Date Considered <b>8/30/05</b>
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	